App No.: 10/812,412 Docket No.: 5438 Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

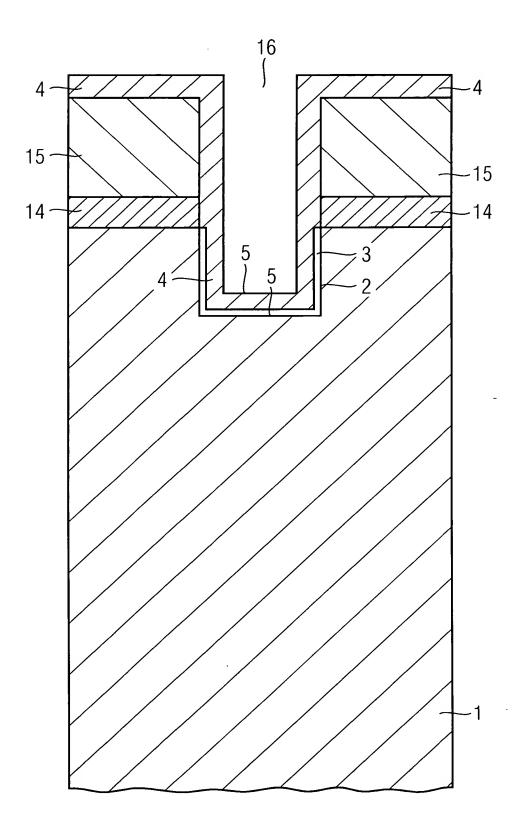
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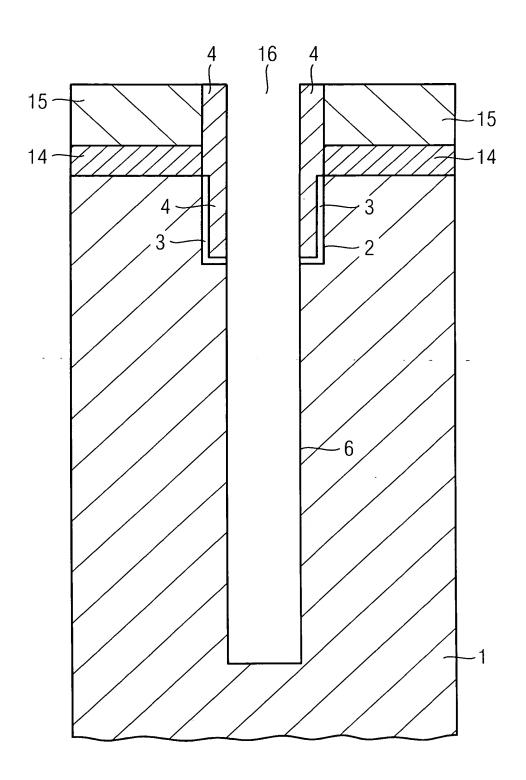
FIG 1A



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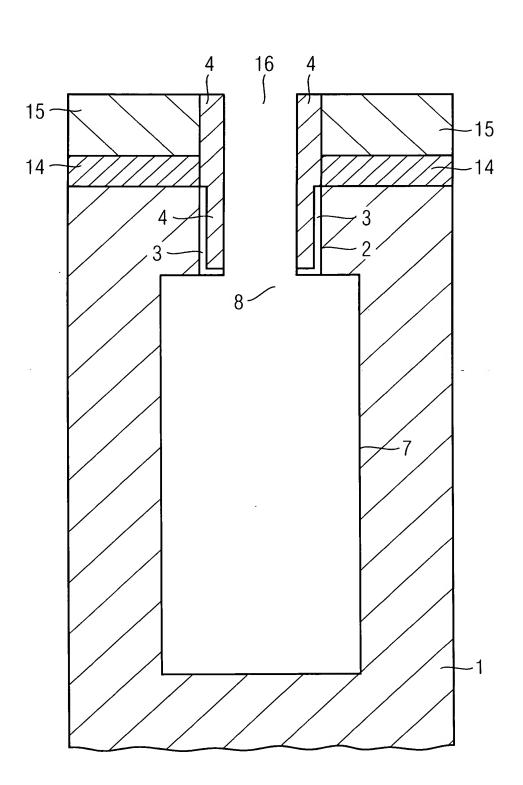
FIG 1B



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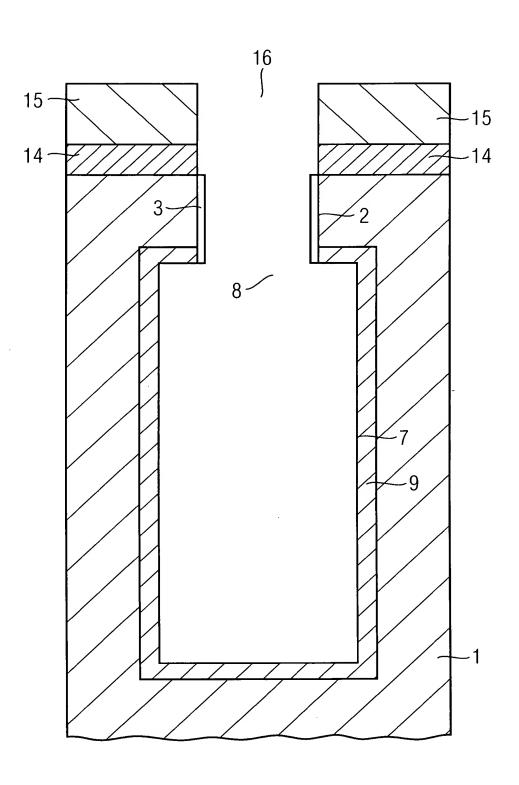
FIG 1C



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FIG 1D

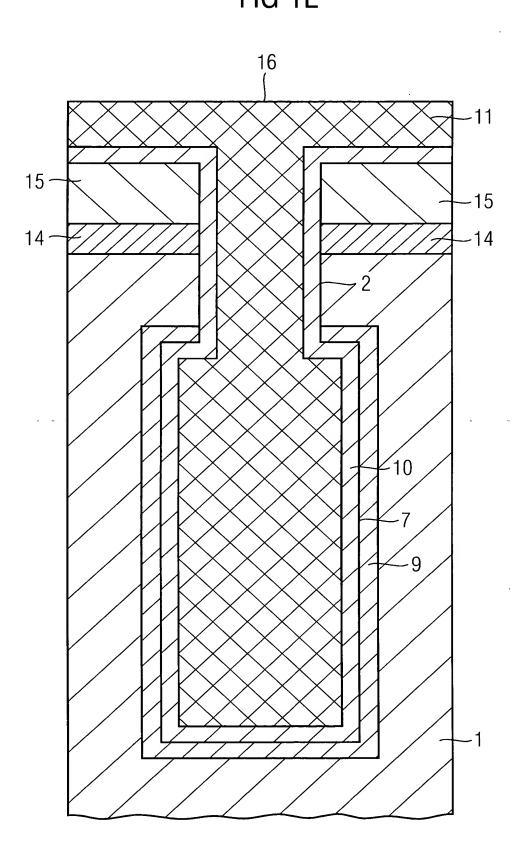


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FIG 1E



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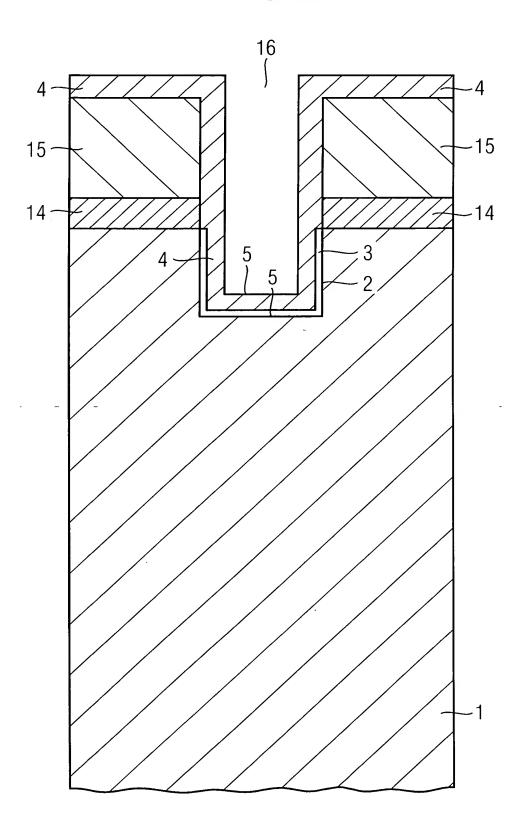
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FIG 2A

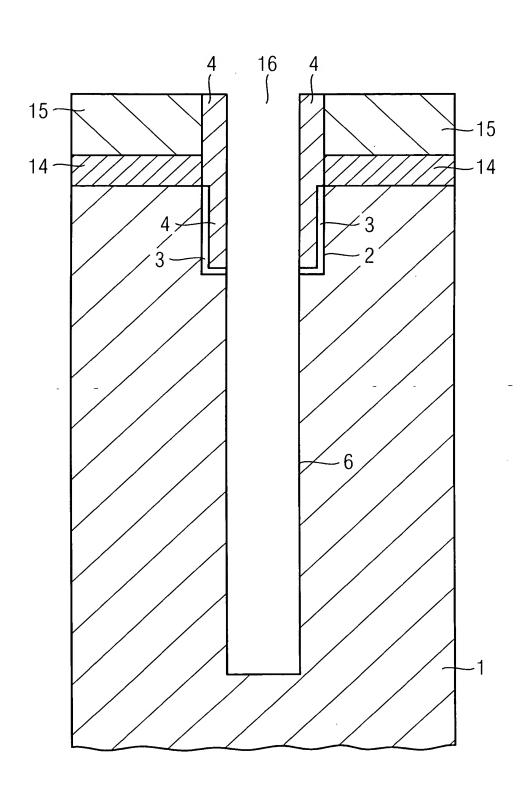


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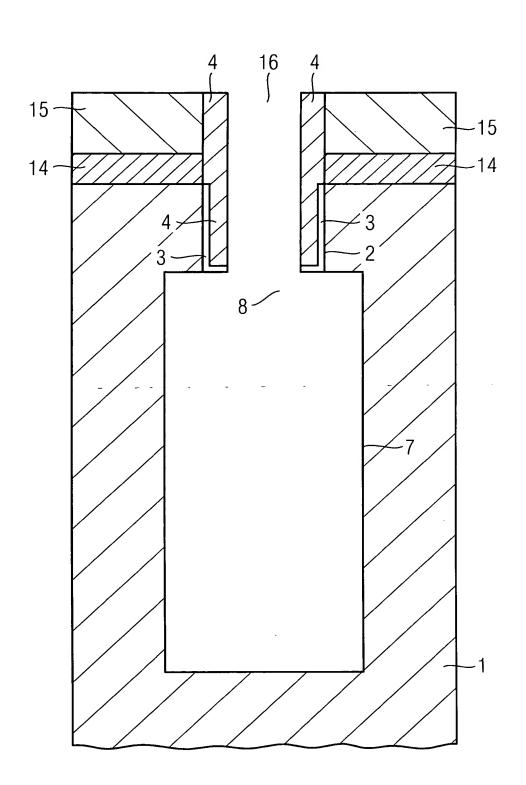
FIG 2B



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FIG 2C



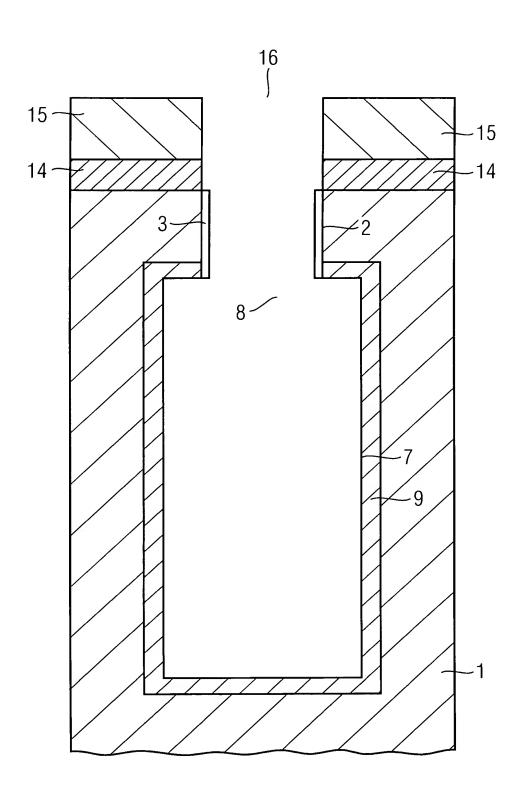
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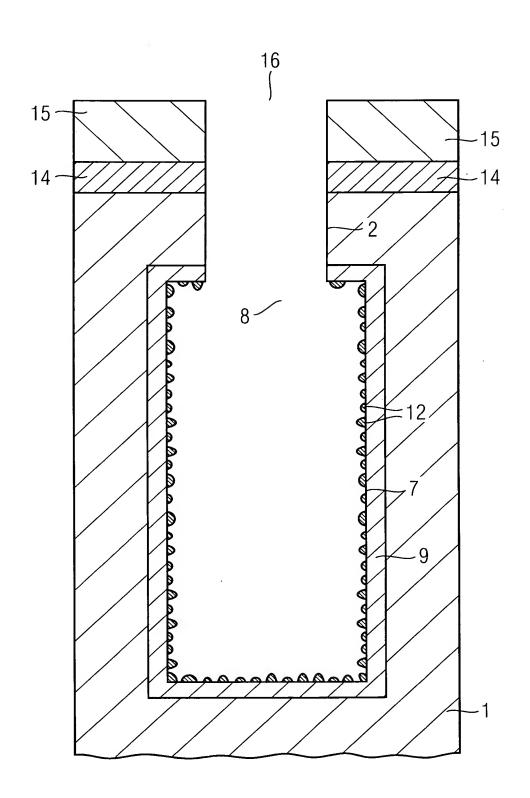
FIG 2D



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FIG 2E

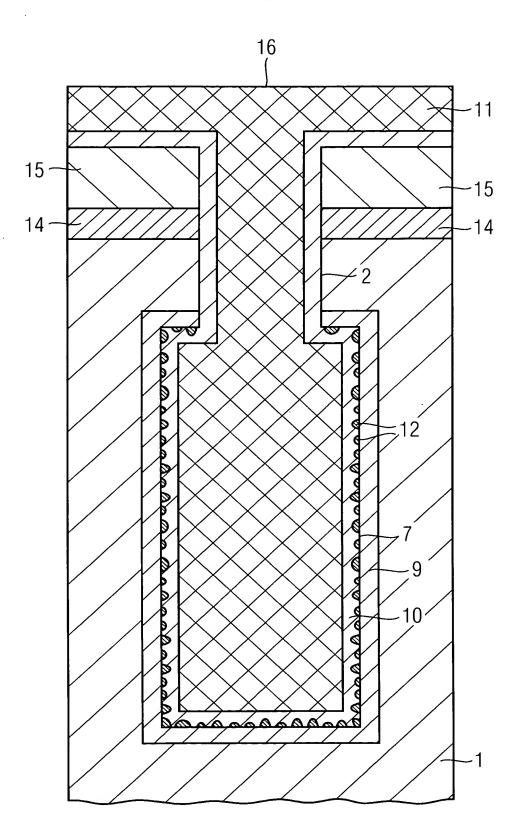


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FIG 2F



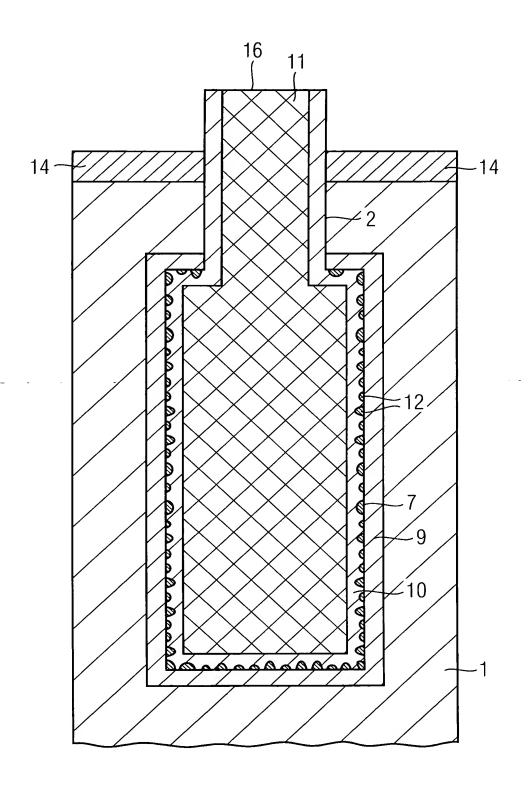
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FIG 2G



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FIG 2H

